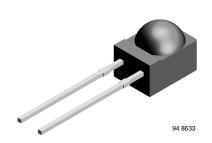
Vishay Semiconductors



Silicon PIN Photodiode, RoHS Compliant



FEATURES

• Package type: leaded

• Package form: side view

• Dimensions (in mm): 4.5 x 5 x 6

• Radiant sensitive area (in mm²): 7.5

· High radiant sensitivity

 Daylight blocking filter matched with 870 nm to 950 nm emitters

· Fast response times

• Angle of half sensitivity: $\varphi = \pm 60^{\circ}$

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



- · High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSFFxxxx series IR emitters

DESCRIPTION

BPV22NF is a PIN photodiode with high speed and high radiant sensitivity in a black, plastic package with side view lens and daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters. The lens achieves 80 % of sensitivity improvement in comparison with flat package. BPV22NFL has long leads, other specifications like BPV22NF.

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.5} (nm)	
BPV22NF	85	± 60	790 to 1050	
BPV22NFL	85	± 60	790 to 1050	

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
BPV22NF	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view	
BPV22NFL	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view, long leads	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	60	V	
Power dissipation	T _{amb} ≤ 25 °C	P _V	215	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	t ≤ 5 s	T _{sd}	260	°C	
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	350	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified



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PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	60			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		2	30	nA
Diode capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _D		70		pF
Serial resistance	V _R = 12 V, f = 1 MHz	R _S		400		Ω
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	Vo		370		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I _k		80		μΑ
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 870 \text{ nm}, \ V_R = 5 \text{ V}$	I _{ra}	55	85		μΑ
Temperature coefficient of I _{ra}	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \ V_R = 10 \text{ V}$	TK _{Ira}		0.1		%/K
Abarlista anastral annaiti iit.	V _R = 5 V, λ = 870 nm	s(λ)		0.57	А	A/W
Absolute spectral sensitivity	$V_R = 5 \text{ V}, \ \lambda = 950 \text{ nm}$	s(λ)		0.6		A/W
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ_{p}		940		nm
Range of spectral bandwidth		λ _{0.5}		790 to 1050		nm
Quantum efficiency	$\lambda = 950 \text{ nm}$	η		90		%
Noise equivalent power	$V_R = 10 \text{ V}, \ \lambda = 950 \text{ nm}$	NEP		4 x 10 ⁻¹⁴		W/√ Hz
Detectivity	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	D*		6 x 10 ¹²		cm√Hz/W
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t _r		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t _f		100		ns
Cut-off frequency	$V_R = 12 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 870 \text{ nm}$	f _c		4		MHz
	$V_{R} = 12 \text{ V}, R_{L} = 1 \text{ k}\Omega, \lambda = 950 \text{ nm}$	f _c		1		MHz

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

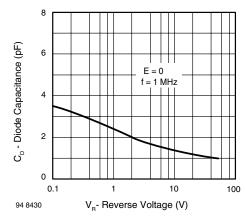


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

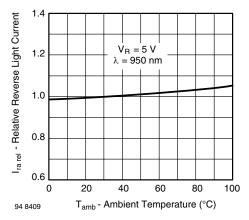


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

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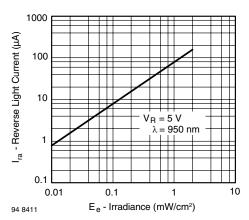


Fig. 3 - Reverse Light Current vs. Irradiance

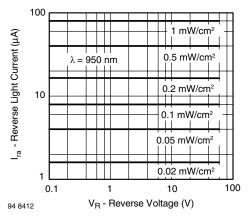


Fig. 4 - Reverse Light Current vs. Reverse Voltage

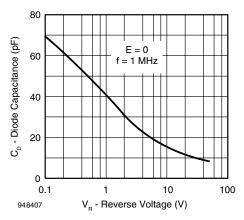


Fig. 5 - Diode Capacitance vs. Reverse Voltage

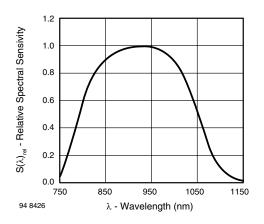


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

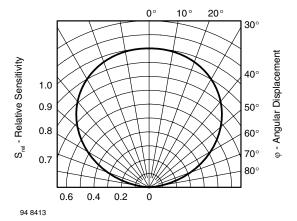
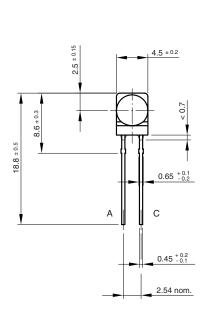


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement



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PACKAGE DIMENSIONS in millimeters: **BPV22NF**



3.2 ± 0.2

(2.4)

R 2.25 (sphere)

3.4 + 0.15

Area not plane

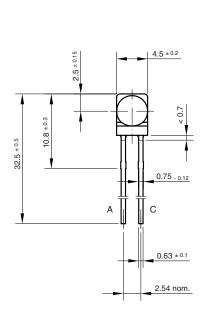
technical drawings according to DIN specifications

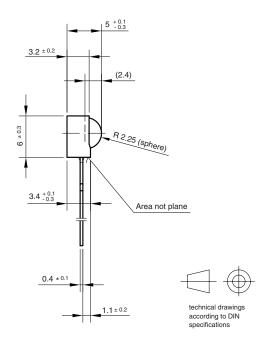
Drawing-No.: 6.544-5199.01-4

Issue: 2; 19.06.01

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PACKAGE DIMENSIONS in millimeters: **BPV22NFL**





Drawing-No.: 6.544-5236.01-4

Issue: 2; 07.07.97

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Revision: 11-Mar-11